

1 ABSTRACT OF THE DISCLOSURE

2 Methods of forming conductive capacitor plugs, methods of forming
3 capacitor contact openings, and methods of forming memory arrays are
4 described. In one embodiment, a conductive capacitor plug is formed
5 to extend from proximate a substrate node location to a location
6 elevationally above all conductive material of an adjacent bit line. In
7 another embodiment, a capacitor contact opening is etched through a
8 first insulative material received over a bit line and a word line
9 substantially selective relative to a second insulative material covering
10 portions of the bit line and the word line. The opening is etched to
11 a substrate location proximate the word line in a self-aligning manner
12 relative to both the bit line and the word line. In another
13 embodiment, capacitor contact openings are formed to elevationally
14 below the bit lines after the bit lines are formed. In a preferred
15 embodiment, capacitor-over-bit line memory arrays are formed.

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